

#### 40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
40V	14.5mΩ @ V <sub>GS</sub> = 10V	43.5A
	25.0mΩ @ V <sub>GS</sub> = 4.5V	34.5A

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON) Minimizes Power Losses
- Wettable Flank for Improved Optical Inspection
- Fast Switching Speed
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4014LPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

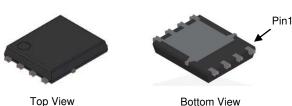
### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

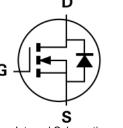
- High Frequency Switching
- Sync Rectification
- DC-DC Converters

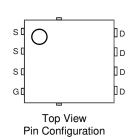
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



PowerDI5060-8 (SWP) (Type UX) **Bottom View** Internal Schematic





### Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4014LPSWQ-13	PowerDI5060-8 (SWP) (Type UX)	2500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



) | = Manufacturer's Marking TH4014LS = Product Type Marking Code YYWW = Date Code Marking  $\overline{YY}$  = Year (ex: 21 = 2021) WW = Week (01 to 53)

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# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6)	T <sub>C</sub> = +25°C	ID	43.5	Α
Continuous Drain Current (Note 6)	T <sub>C</sub> = +100°C		30.8	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	43.5	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		l <sub>DM</sub>	170	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Ism	170	Α
Avalanche Current, L=0.1mH		las	19.8	Α
Avalanche Energy, L=0.1mH		Eas	19.6	mJ

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	38	°C/W
Total Power Dissipation (Note 6)	T <sub>C</sub> = +25°C	PD	46.9	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	3.2	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

			_				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	40	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	$V_{DS} = 32V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Daggan	_	10.8	14.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialii-Source Off-Nesistance	Rds(on)	_	17.0	25.0	11122	$V_{GS} = 4.5V, I_{D} = 10A$	
Diode Forward Voltage	VsD	_	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	750			V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	225		pF		
Reverse Transfer Capacitance	Crss	_	21				
Gate Resistance	Rg	_	1.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Qg	_	5.7				
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	11.2		nC	Vpp = 20V. Ip = 20A	
Gate-Source Charge	Qgs	_	2.0	_	ПС	VDD = 20V, ID = 20A	
Gate-Drain Charge	$Q_{gd}$	_	2.2				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.5	_		$V_{GS} = 10V, V_{DD} = 20V,$ $R_g = 1.6\Omega, I_D = 20A$	
Turn-On Rise Time	tr	_	4.6	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	12.4	_	ns		
Turn-Off Fall Time	tr	_	4.9	_			
Body Diode Reverse Recovery Time	trr	_	11.3	_	ns	L 150 di/da 1000/iva	
Body Diode Reverse Recovery Charge	Qrr	_	9.5	_	nC	I <sub>F</sub> = 15A, di/dt = 400A/μs	

Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



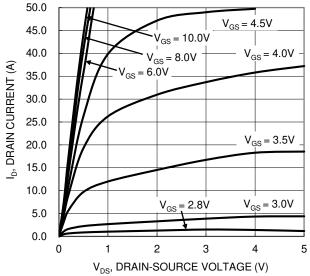


Figure 1. Typical Output Characteristic

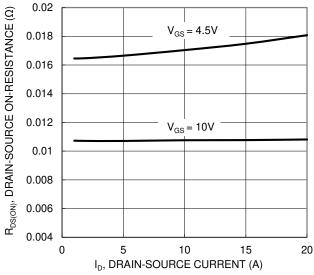


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

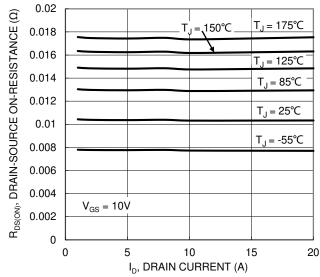
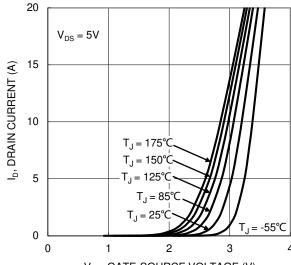


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

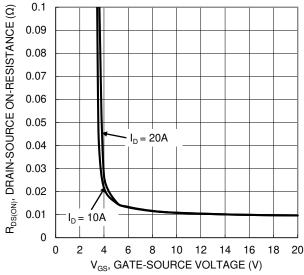


Figure 4. Typical Transfer Characteristic

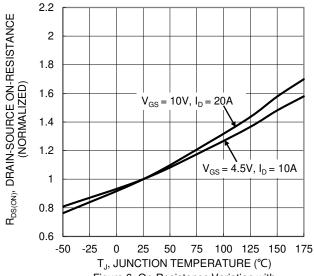


Figure 6. On-Resistance Variation with Junction Temperature



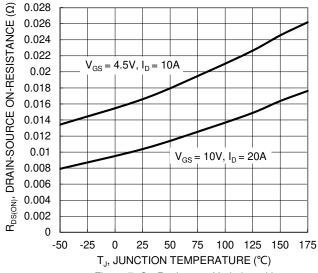
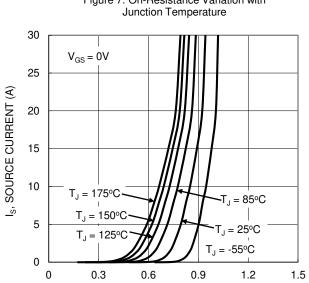
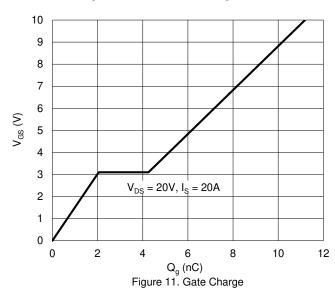


Figure 7. On-Resistance Variation with



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



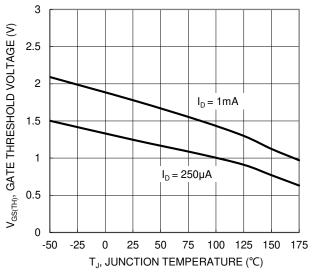
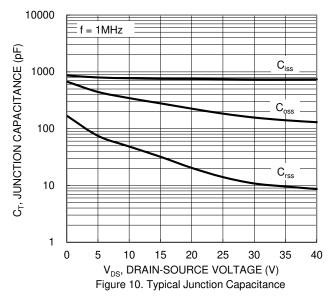


Figure 8. Gate Threshold Variation vs. Junction Temperature



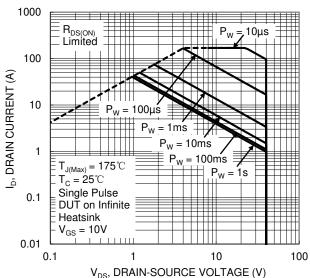


Figure 12. SOA, Safe Operation Area



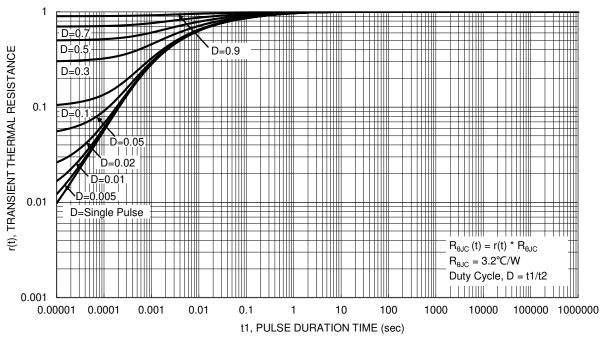


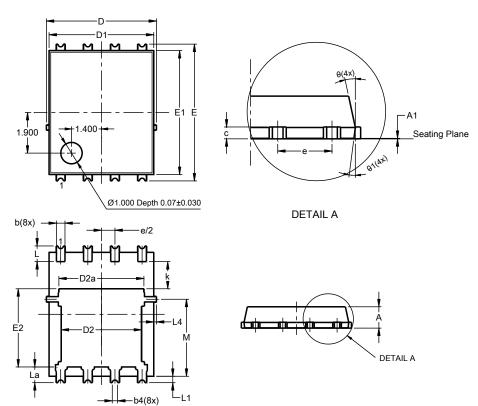
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)

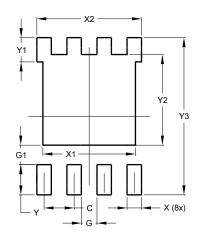


PowerDI5060-8 (SWP) (Type UX)				
Dim	Min Max		Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4		).25REF	•	
C D	0.230	0.330	0.277	
	5	.15 BS(	)	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
Е	6.40 BSC			
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е	1	.27BSC		
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value			
Dilliciololio	(in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	4.420			
Y	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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